

Product Summary

BV_{DS}	$R_{DS(ON)}$ max	I_D $T_A = +25^\circ\text{C}$
100V	220m Ω @ $V_{GS} = 10\text{V}$	2.3A
	250m Ω @ $V_{GS} = 4.5\text{V}$	2.1A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMN10H220LEQ](#))**

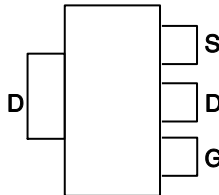
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 ^(e3)
- Weight: 0.112 grams (Approximate)

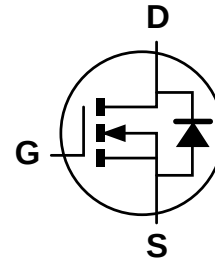
SOT223



Top View



Pin Out - Top View



Equivalent Circuit

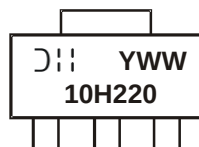
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN10H220LE-13	Standard	SOT223	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

SOT223



DII = Manufacturer's Marking
10H220 = Marking Code
YWW = Date Code Marking
Y or Y = Year (ex: 7 = 2017)
WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	100	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	T _A = +25°C	I _D	2.3	A
	T _A = +70°C		1.8	
	T _C = +25°C	I _D	6.2	A
	T _C = +70°C		4.9	
Maximum Continuous Body Diode Forward Current (Note 5)		I _S	1.5	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		I _{DM}	8	A

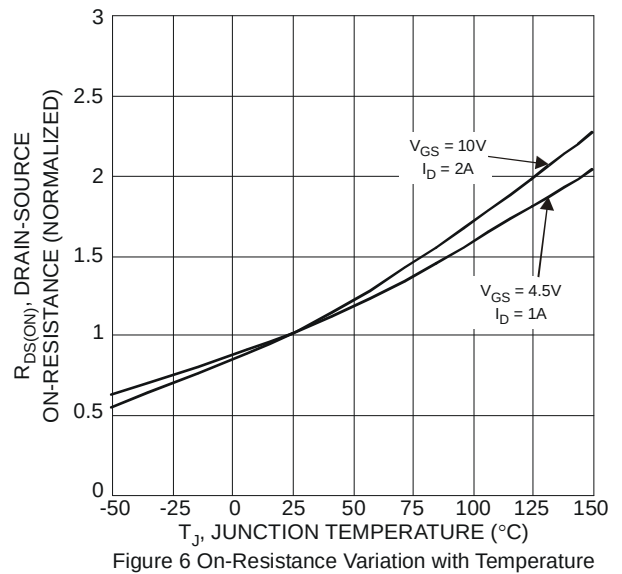
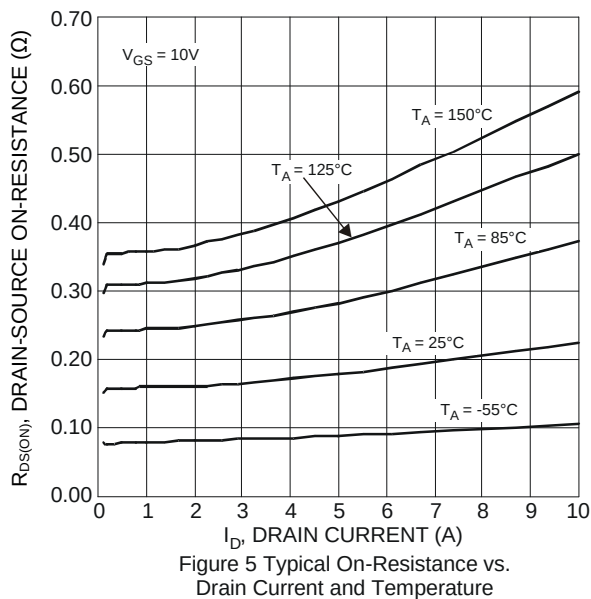
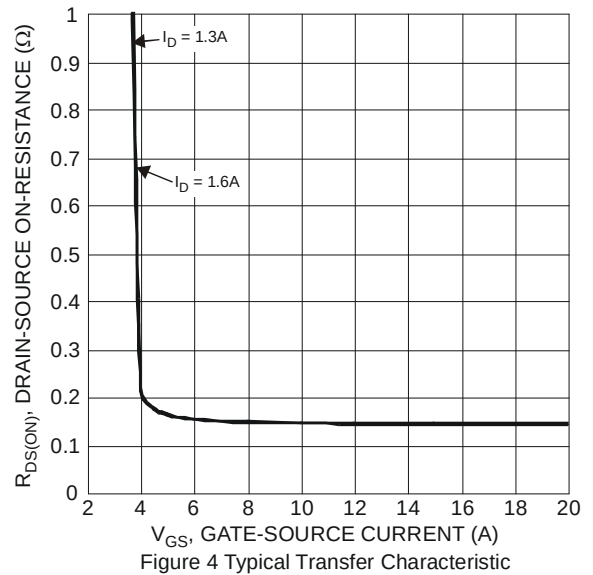
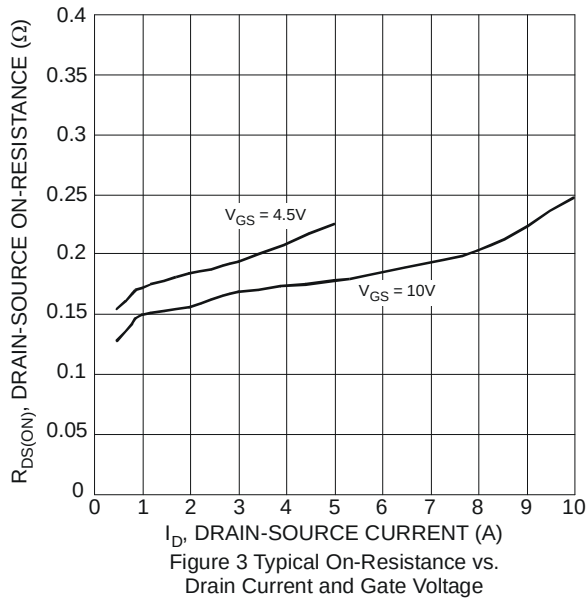
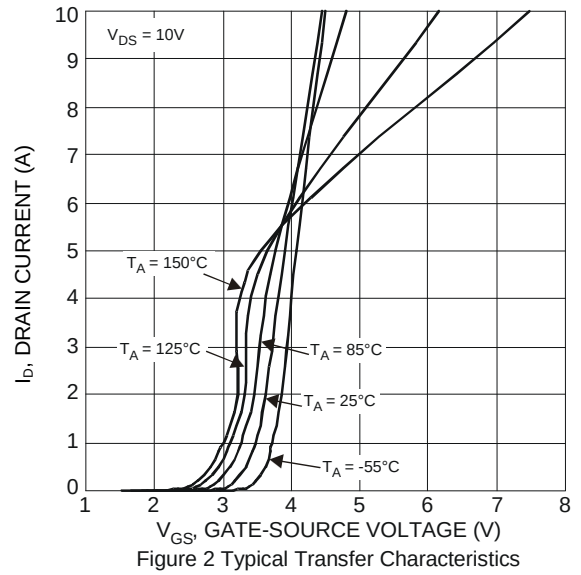
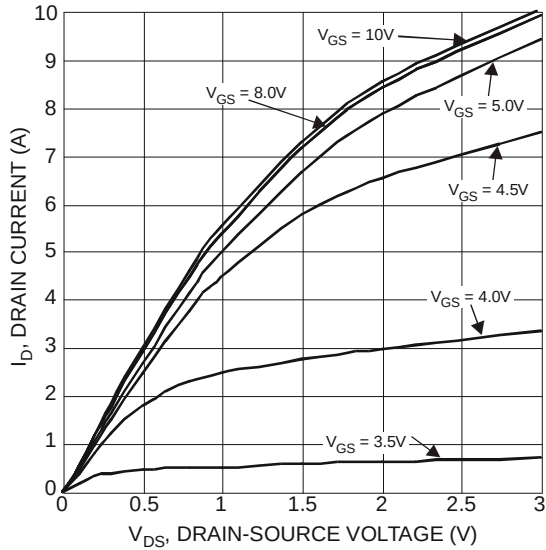
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

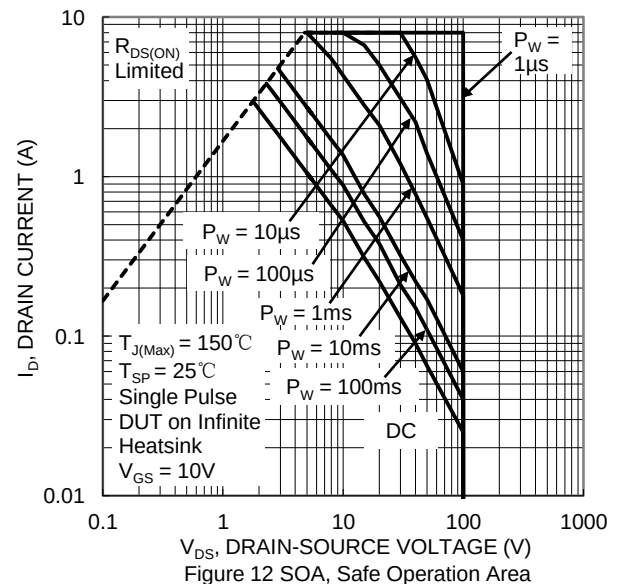
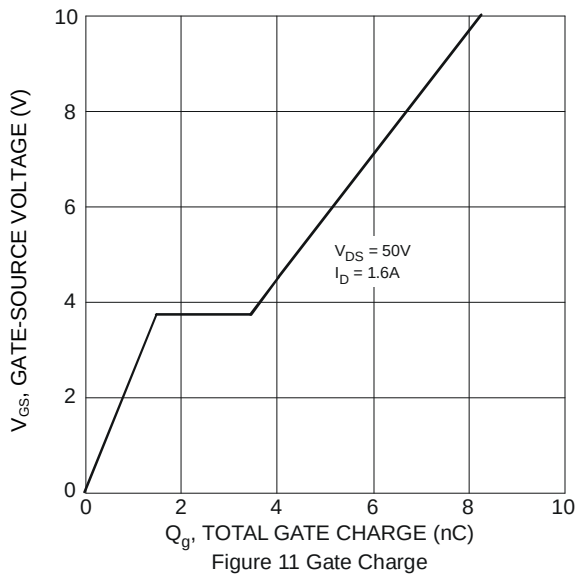
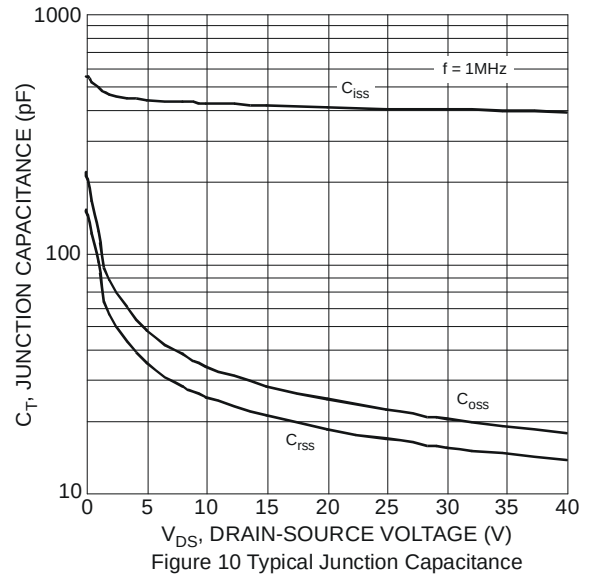
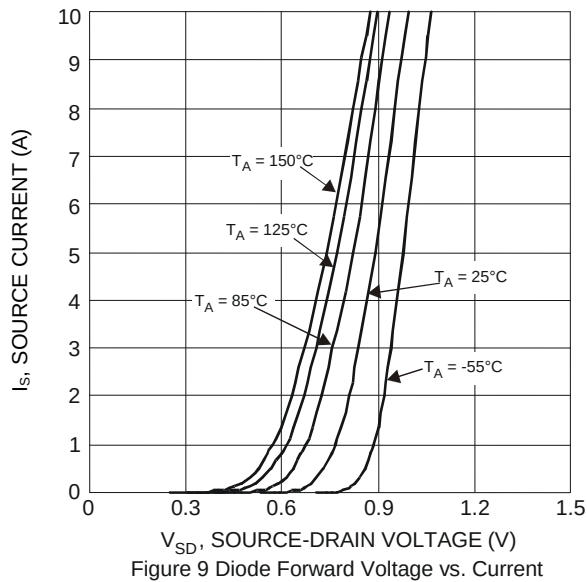
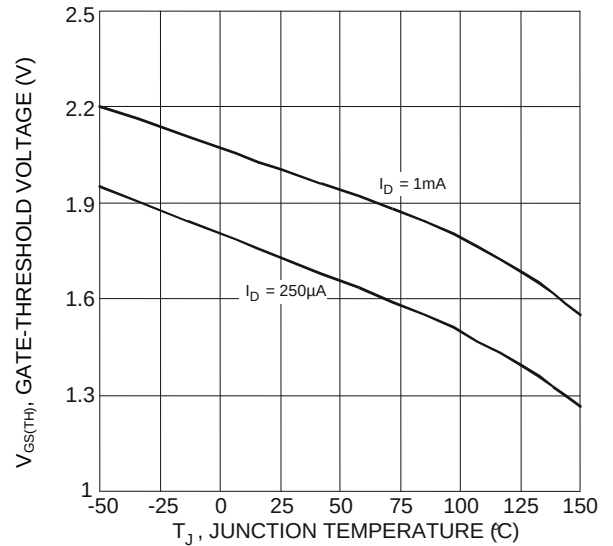
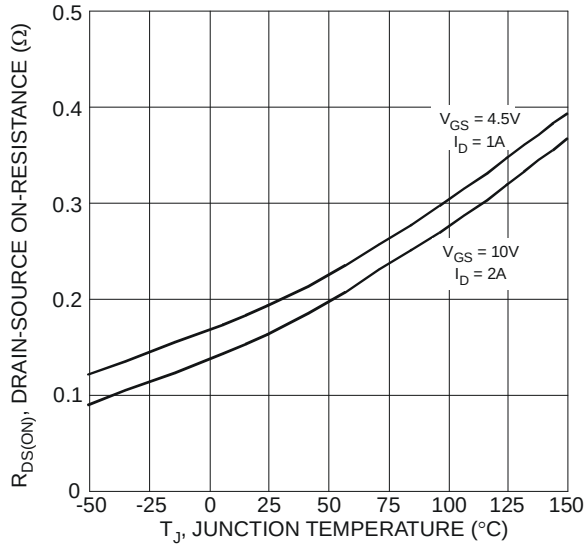
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.8	W
	T _A = +70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 5)		R _{θJA}	69	°C/W
Total Power Dissipation (Note 5)	T _C = +25°C	P _D	14	W
	T _C = +70°C		8.7	
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	8.7	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

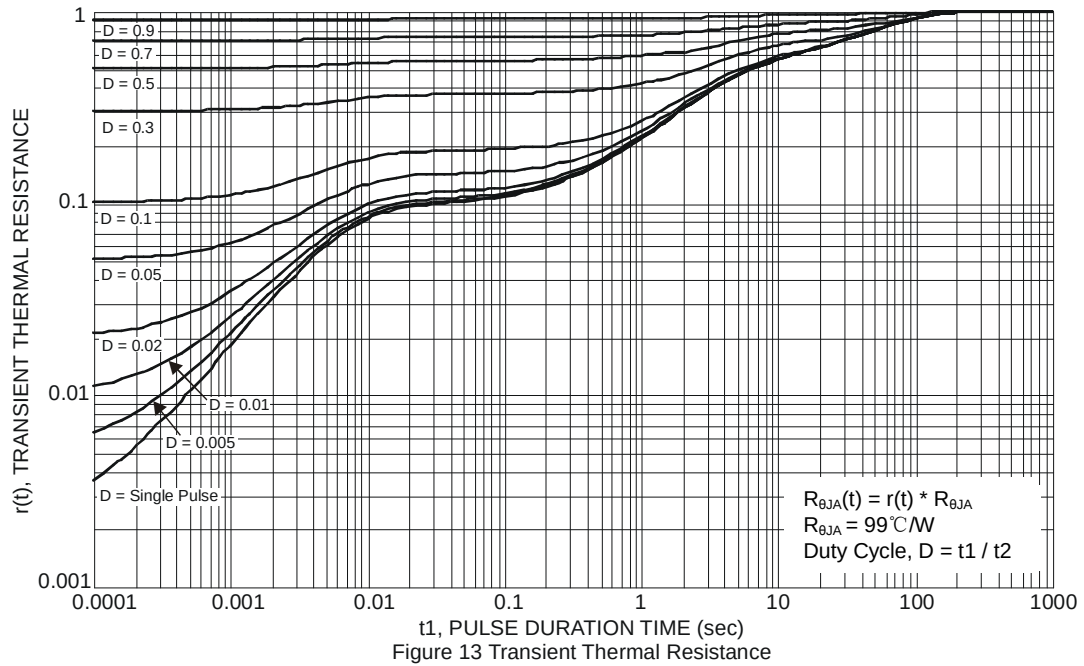
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	1	1.7	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	155	220	mΩ	V _{GS} = 10V, I _D = 1.6A
		—	190	250		V _{GS} = 4.5V, I _D = 1.3A
Diode Forward Voltage	V _{SD}	—	0.8	1.5	V	V _{GS} = 0V, I _S = 1.1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	401	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	22	—		
Reverse Transfer Capacitance	C _{rss}	—	17	—		
Gate Resistance	R _g	—	2.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	4.1	—	nC	V _{DS} = 50V, I _D = 1.6A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	8.3	—		
Gate-Source Charge	Q _{gs}	—	1.5	—		
Gate-Drain Charge	Q _{gd}	—	2	—		
Turn-On Delay Time	t _{D(ON)}	—	6.8	—	ns	V _{DS} = 50V, V _{GS} = 4.5V, R _G = 6.8Ω, I _D = 1.0A
Turn-On Rise Time	t _R	—	8.2	—		
Turn-Off Delay Time	t _{D(OFF)}	—	7.9	—		
Turn-Off Fall Time	t _F	—	3.6	—		
Reverse Recovery Time	t _{RR}	—	17	—	ns	I _S = 1.1A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	9.8	—	nC	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
 6. Short duration pulse test used to minimize self-heating effect.
 7. Guaranteed by design. Not subject to production testing.



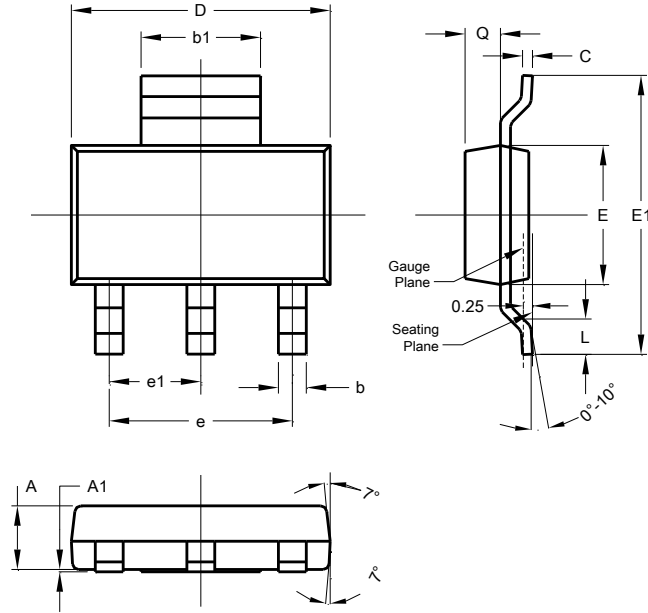




Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223

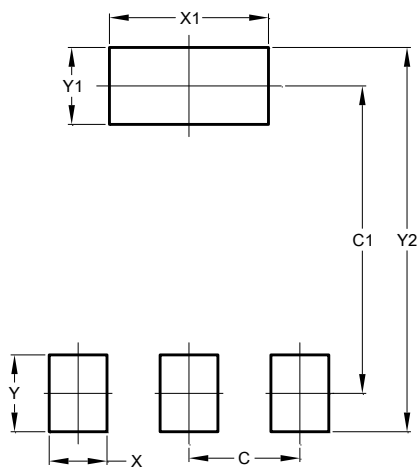


SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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